YL-PSC850nM(120)-2mW Rev 2.0

850nm RCLED Chip

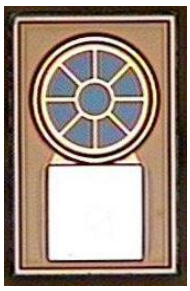
Features

: 850 nm wavelength range

: Enhanced coupling efficiency

: Other configurations available on request

Description



Applications

: Data Link Communication

: Sensors

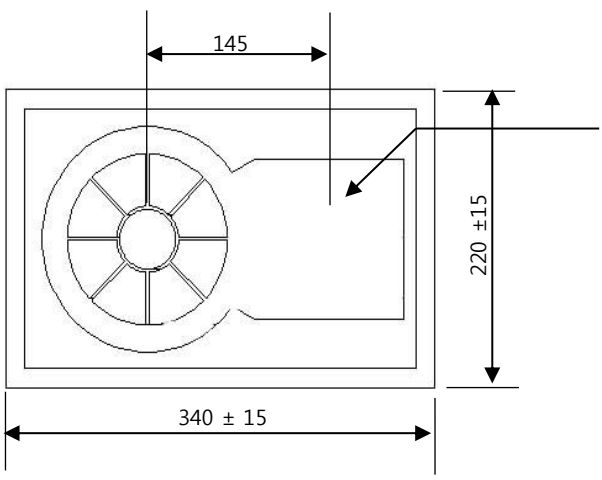
: Industrial applications

Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	-40 to 100 ℃
Operating Temperature	-20 to 85 ℃
Continuous Forward Current	40mA
Pulse Current *	300mA
Continuous Reverse Voltage	5V (@10μA)

***** pulse width : 4μs , duty cycle : 1 ~ 5%

Dimensions



Anode pad (120x120)

Diameter of Emission area : Ø 128 ㎛

Unit : ㎛

Die Height : 250±15㎛

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Electro-Optics Characteristics (T_a=25℃ unless otherwise stated)

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Total Radiant Flux	Φ_o	1.5	2		mW	I_f=30mA
Peak Wavelength	λ_P	840	850	860	nm	I_f=30mA
Spectral Width	$\Delta\lambda$		20		nm	I_f=30mA, FWHM
Beam Divergence	Θ		120		Deg.	I_f=30mA, FWHM
Forward Voltage	V_f		1.6		V	I_f=30mA

Test Data were measured in TO header of wire bonded chip

Value is referenced to the vender's measurement system (correlation to customer product is required).

Thermal Characteristics

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
P_o Temp Coefficient	$\Delta P_o / \Delta T$		-0.5		%/ ℃	-20℃ ~ 85℃ at I_f=30mA
λ_P Temp Coefficient	$\Delta\lambda / \Delta T$		0.06		nm/℃	-20℃ ~ 85℃ at I_f=30mA

Notes

* These specifications are subject to change without notice.

NOTICE	The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product